



# **SNS COLLEGE OF TECHNOLOGY**

**Coimbatore-35**  
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## **DEPARTMENT OF ELECTRONICS & COMMUNICATION ENGINEERING**

### **19ECT312 – EMBEDDED SYSTEM DESIGN**

III YEAR/ VI SEMESTER  
1

#### **UNIT 1 – INTRODUCTION TO EMBEDDED SYSTEMS**

#### **TOPIC 1.8 – EMBEDDED MEMORY**



# EMBEDDED MEMORY



- **Memory Hierarchy** **Cache Memory** –
- **Different types of Cache Mappings** –
- **Cache Impact on System**

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**Performance** **Dynamic Memory** –

- **Different types of Dynamic RAMs** **?**

**Memory Management Unit**



# EMBEDDED MEMORY



Memory Hierarchy Objective is to use inexpensive, fast memory

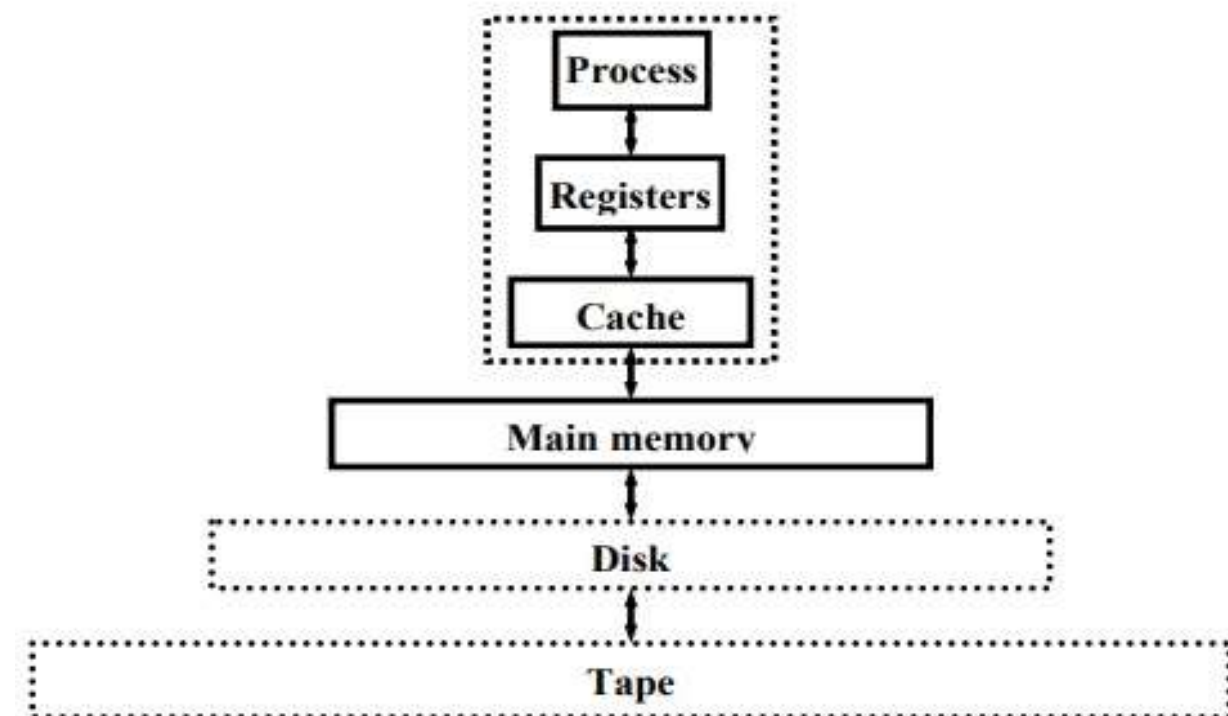
- Main memory ☐

Large, inexpensive, slow memory stores entire program and data

- Cache ☐

Small, expensive, fast memory stores copy of likely accessed parts of larger memory ☐ Can be multiple levels of cache

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The memory Hierarchy



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## Cache

- **Usually designed with SRAM** [?]  
faster but more expensive than DRAM
- **Usually on same chip as processor** [?]  
space limited, so much smaller than off-chip main memory [?]  
Faster access (1 cycle vs. several cycles for main memory)
- **Cache operation** [?]  
Request for main memory access (read or write) [?]  
First, check cache for copy [?]  
cache hit  
• copy is in cache, quick access  
• cache miss - copy not in cache, read address and possibly its neighbors into cache
- **Several cache design choices** [?]  
cache mapping, replacement policies, and write techniques

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## Cache Mapping

- Necessary as there are far fewer number of available cache addresses than the memory
  - Are address' contents in cache?
  - Cache mapping used to assign main memory address to cache address and determine hit or miss
    - Three basic techniques:
      1. Direct mapping
      2.  Fully associative mapping
      3.  Set-associative mapping
- Caches partitioned into indivisible blocks or lines of adjacent memory addresses   
usually 4 or 8 addresses per line



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## Direct Mapping

- Main memory address divided into 2 fields [?]

Index which contains

- cache address
- number of bits determined by cache size [?]

### -Tag

- compared with tag stored in cache at address indicated by index
- - if tags match, check valid bit

- Valid bit [?]

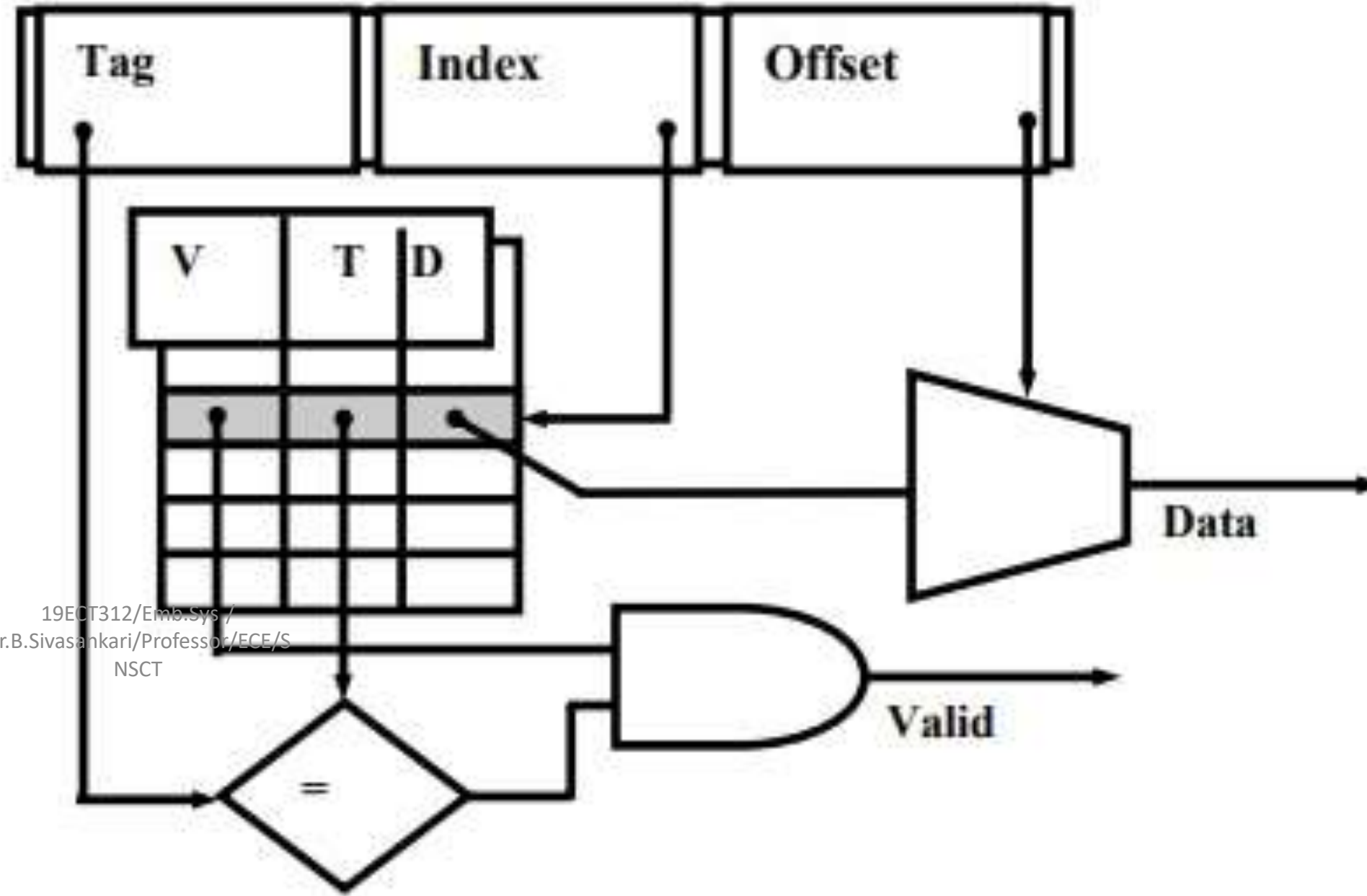
- indicates whether data in slot has been loaded from memory

- Offset

- [?] used to find particular word in cache line



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**Direct Mapping**

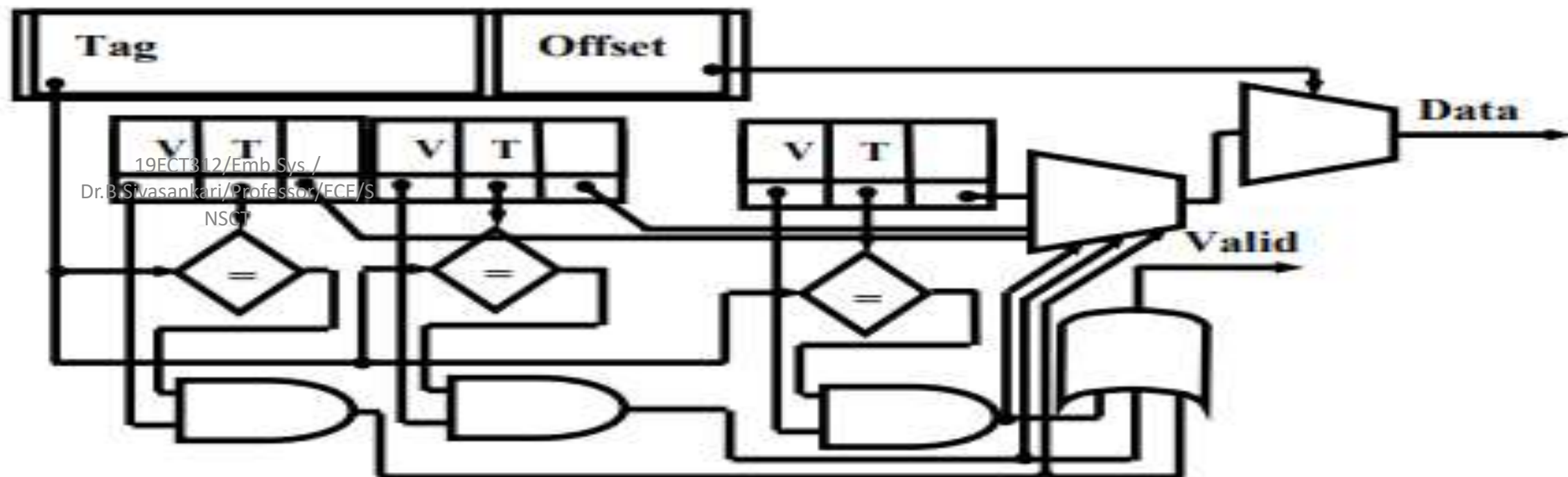


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## Fully Associative Mapping

- Complete main memory address stored in each cache address
- All addresses stored in cache simultaneously compared with desired address
- Valid bit and offset same as direct mapping



**Fully Associative Mapping**





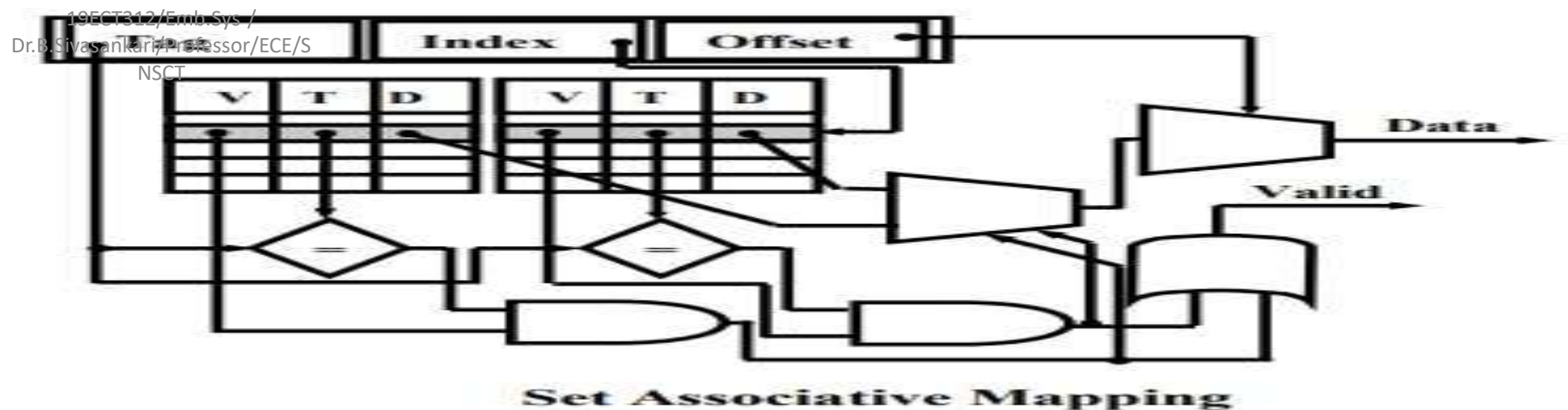
# EMBEDDED MEMORY



## Set-Associative Mapping

- Compromise between direct mapping and fully associative mapping
- Index same as in direct mapping
- But, each cache address contains content and tags of 2 or more memory address locations
- Tags of that set simultaneously compared as in fully associative mapping
- Cache with set size N called N-way set-associative ☐

2-way, 4-way, 8-way are common





# EMBEDDED MEMORY



## Cache-Replacement Policy

- Technique for choosing which block to replace ☐
  - when fully associative cache is full ☐
  - when set-associative cache's line is full
- Direct mapped cache has no choice
- Random ☐
  - replace block chosen at random
- LRU: **least-recently used** ☐
  - replace block not accessed for longest time
- FIFO: first-in-first-out ☐
  - push block onto queue when accessed ☐
  - choose block to replace by popping queue



# EMBEDDED MEMORY



## Cache Write Techniques

- When written, data cache must update main memory
- **Write-through** ☐
  - write to main memory whenever cache is written to ☐
  - easiest to implement
  - ☐ processor must wait for slower main memory write ☐
  - potential for unnecessary writes
- **Write-back** ☐
  - main memory only written when “dirty” block replaced ☐
  - extra dirty bit for each block set when cache block written to ☐
  - reduces number of slow main memory writes

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## Cache Impact on System Performance

- Most important parameters in terms of performance:
  - ☐ Total size of cache
    - total number of data bytes cache can hold
    - tag, valid and other house keeping bits not included in total ☐
  - Degree of associativity ☐
  - Data block size

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Larger caches achieve lower miss rates but higher access cost

- e.g.,
  - 2 Kbyte cache: miss rate = 15%, hit cost = 2 cycles, miss cost = 20 cycles
    - avg. cost of memory access  
 $= (0.85 * 2) + (0.15 * 20) = 4.7$  cycles
  - 4 Kbyte cache: miss rate = 6.5%, hit cost = 3 cycles, miss cost will not change
    - avg. cost of memory access =  $(0.935 * 3) + (0.065 * 20) = 4.105$  cycles **improvement**
  - 8 Kbyte cache: miss rate = 5.565%, hit cost = 4 cycles, miss cost will not change
    - avg. cost of memory access =  $(0.94435 * 4) + (0.05565 * 20) = 4.8904$  cycles

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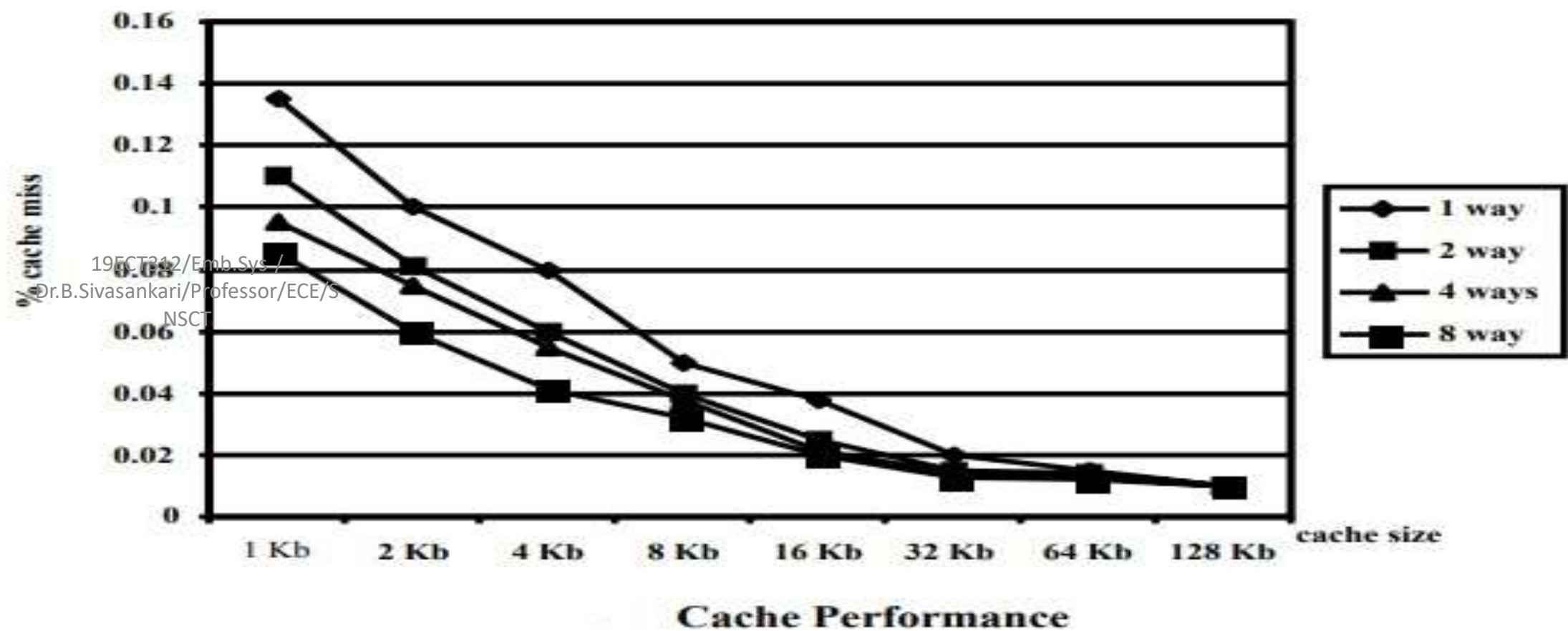


## Cache Performance Trade-Offs

- Improving cache hit rate without increasing size ☐

Increase line size ☐

Change set-associativity





# EMBEDDED MEMORY



## Advanced RAM

DRAMs commonly used as main memory in processor based embedded systems ☐

high capacity, low cost

**Many variations of DRAMs proposed** ☐

need to keep pace with processor speeds

1. **FPM DRAM:** fast page mode DRAM ☐
2. **EDO DRAM:** extended data out DRAM ☐  
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3. **SDRAM/ESDRAM:** synchronous and enhanced synchronous DRAM ☐
4. **RDRAM:** rambus DRAM



# EMBEDDED MEMORY



## Basic DRAM

- Address bus multiplexed between row and column components
- Row and column addresses are latched in, sequentially, by strobing ras (row address strobe) and cas (column address strobe) signals, respectively
- Refresh circuitry can be external or internal to DRAM device 
  - strobcs consecutive memory address periodically causing memory content to be refreshed
- Refresh circuitry disabled during read or write operation

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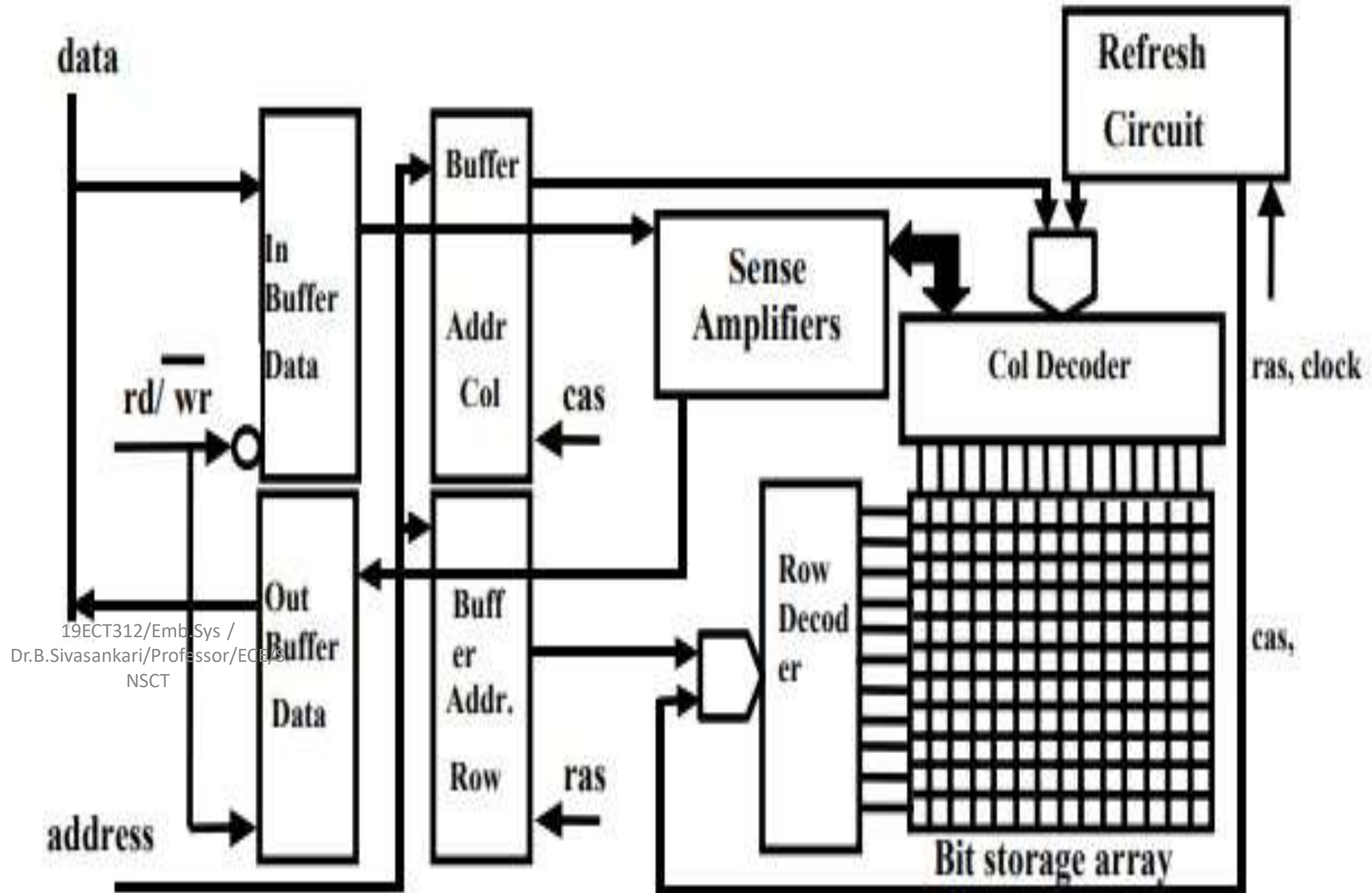
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The Basic Dynamic RAM Structure



# EMBEDDED MEMORY



## Fast Page Mode DRAM (FPM DRAM)

- Each row of memory bit array is viewed as a page
- Page contains multiple words
- Individual words addressed by column address
- Timing diagram: 

row (page) address sent

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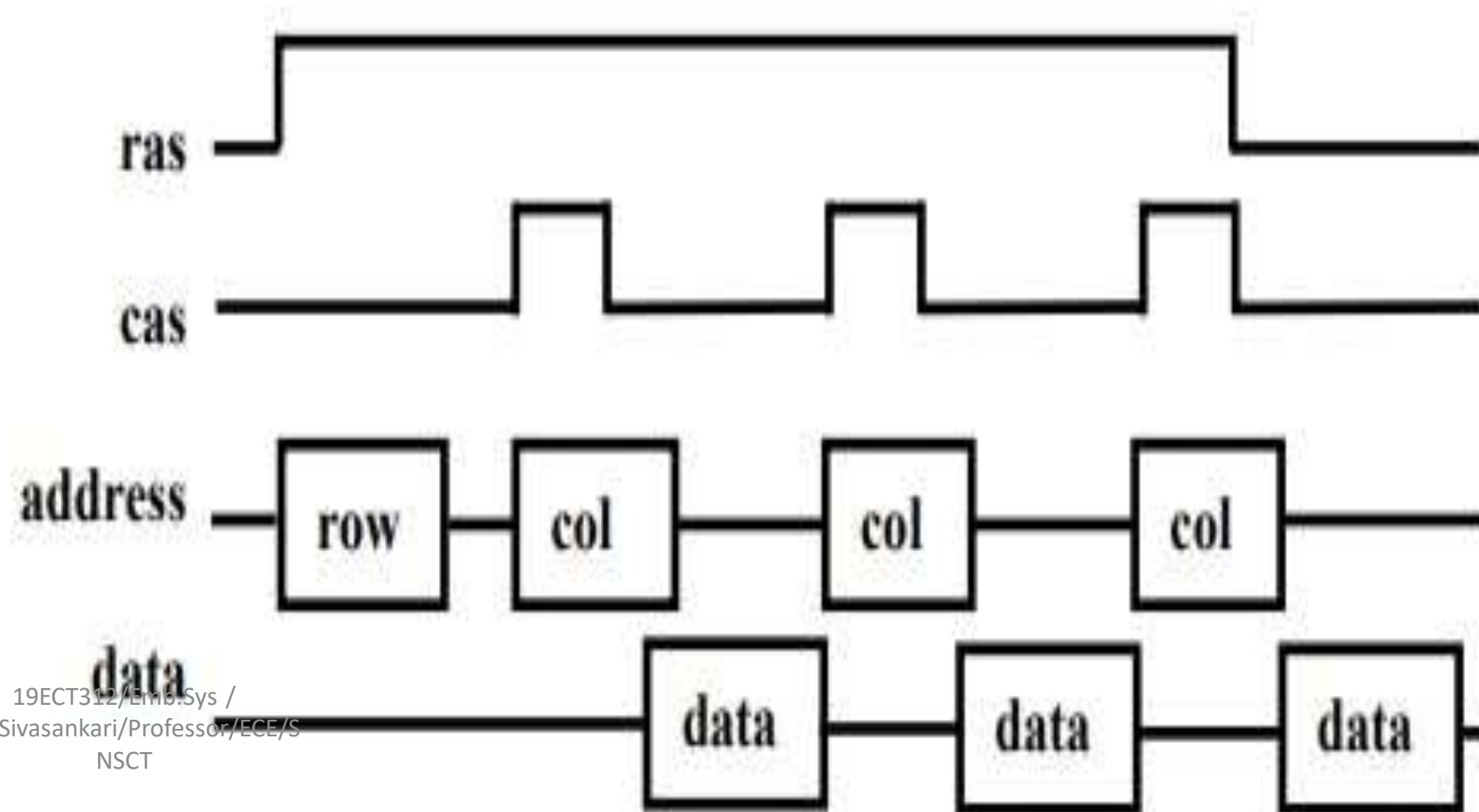
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 words read consecutively by sending column address for

each Extra cycle eliminated on each read/write of words from same



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The timing diagram in FPM DRAM



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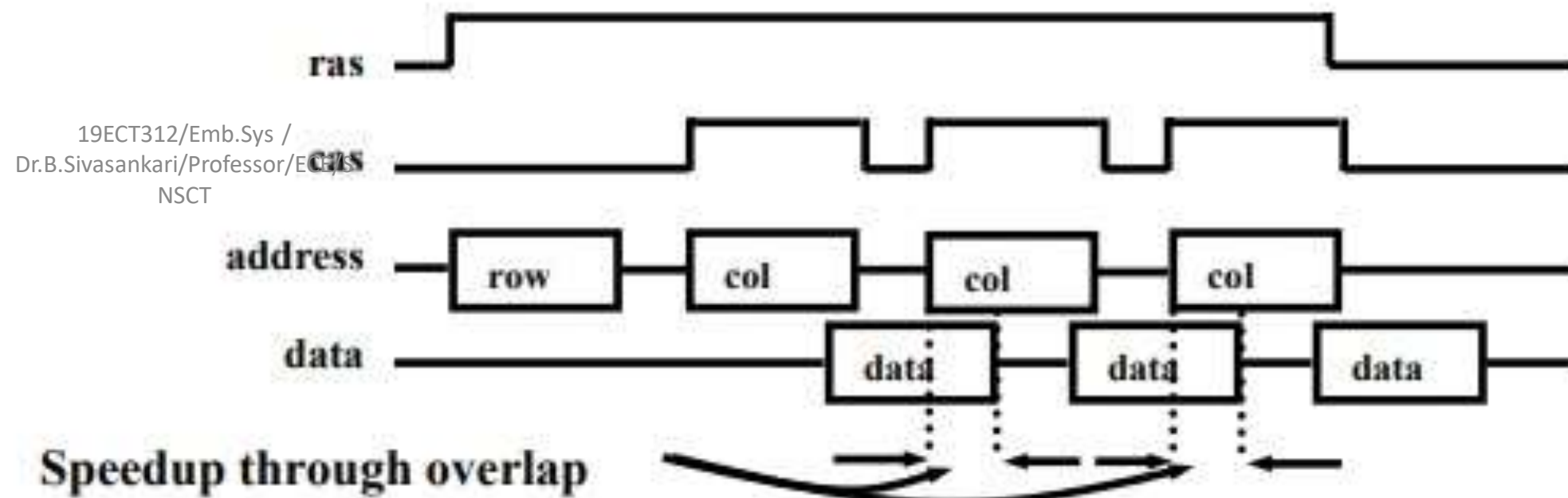


## Extended data out DRAM (EDO DRAM)

- Improvement of FPM DRAM
- Extra latch before output buffer

allows strobing of cas before data read operation completed

- Reduces read/write latency by additional cycle



The timing diagram in EDORAM

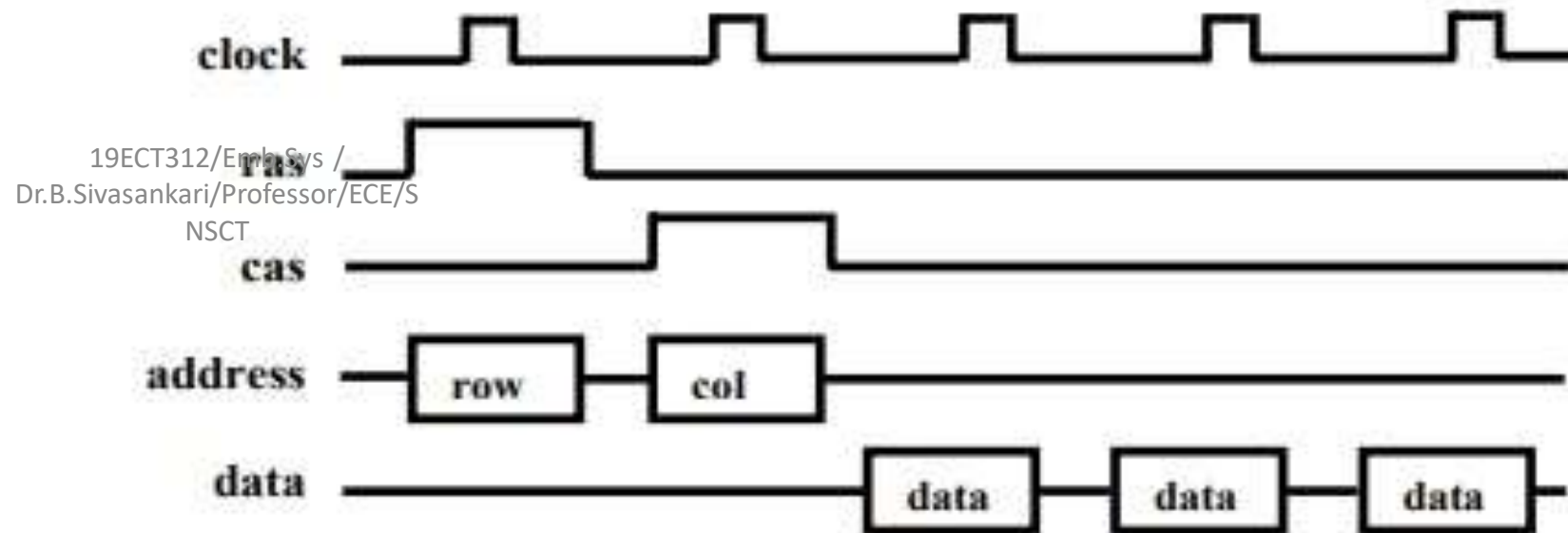


# EMBEDDED MEMORY



## (S)ynchronous and Enhanced Synchronous (ES) DRAM

- SDRAM latches data on active edge of clock
- Eliminates time to detect ras/cas and rd/wr signals
- A counter is initialized to column address then incremented on active edge of clock to access consecutive memory locations
- ESDRAM improves SDRAM 
  - added buffers enable overlapping of column addressing
  - faster clocking and lower read/write latency possible



The timing diagram in SDRAM



## Rambus DRAM (RDRAM)



- More of a bus interface architecture than DRAM architecture
- Data is latched on both rising and falling edge of clock
- Broken into 4 banks each with own row decoder can have 4 pages open at a time
- Capable of very high throughput

## DRAM Integration Problem

- SRAM easily integrated on same chip as processor
- DRAM more difficult

Different chip making process between DRAM and conventional logic

### Goal of conventional logic (IC) designers: -

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minimize parasitic capacitance to reduce signal propagation delays and power consumption

### •Goal of DRAM designers: -

create capacitor cells to retain stored information

Integration processes beginning to appear



# EMBEDDED MEMORY



## Memory Management Unit (MMU)

- Duties of MMU
  - Handles DRAM refresh, bus interface and arbitration
  - Takes care of memory sharing among multiple processors
  - Translates logic memory addresses from processor to physical memory addresses of DRAM
- Modern CPUs often come with MMU built-in
- Single-purpose processors can be used

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# SUMMARY & THANK YOU

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